

INFORMATION DISCLOSURE CITATION

Atty. Docket No.	04329.3139	Serial No.	
Applicant	Mitsuaki IZUHA et al.		
Filing Date	September 12, 2003	Group:	

U.S. PATENT DOCUMENTS						
Examiner Initial*	Document Number	Issue Date (Pub. Date)	Name	Class	Sub Class	Filing Date If Appropriate
SR ↓	5,656,859	08/12/1997	Murakoshi et al.			
	5,770,512	06/23/1998	Murakoshi et al.			
	2002/0130393 A1	(09/19/2002)	Takayanagi et al.			

FOREIGN PATENT DOCUMENTS						
	Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
SR	9-139511	05/27/1997	Japan			No
SR	3219996	08/10/2001	Japan			No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
SR	Ku et al.; "HIGH PERFORMANCE pMOSFETs WITH Ni(Si _x Ge _{1-x})/POLY-Si _{0.8} Ge _{0.2} GATE"; Symposium on VSLI Technology Digest of Technical Papers, (2000)

Examiner	<i>[Signature]</i>	Date Considered	12/07/05
*Examiner:	Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		
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OMB No. 0651-0011

INFORMATION DISCLOSURE CITATION

Atty. Docket No.	4329.3139	Appln. No.	10/660,555
Applicant	Izuha et al.		
Filing Date	September 12, 2003	Group:	Unknown

U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

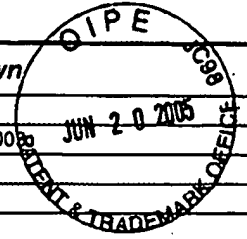
Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
11-214680	8/6/99	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>SA</i>	Maa et al., "Stability Improvement of Nickel Silicide with Co Interlayer on Si, Polysilicon and SiGe," Mat. Res. Soc. Symp. Proc. (2001), 670:K6.9.1-K6.9.6
<i>SA</i>	Wang et al., "Silicide formation and stability of Ti/SiGe and Co/SiGe," Thin Solid Films (1995), pp. 555-560

Examiner <i>SA</i>	Date Considered <i>12/07/05</i>
*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	
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IDS Form PTO/SB/08: Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	10/660,555
				Filing Date	September 12, 2005
				First Named Inventor	Mitsuaki Izuha
				Art Unit	2811
				Examiner Name	VU, Quang D.
Sheet	1	of	1	Attorney Docket Number	4329.3139



U.S. PATENTS AND PUBLISHED U.S. PATENT APPLICATIONS					
Examiner Initials	Cite No. ¹	Document Number	Issue or Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			

Note: Copies of the U.S. Patent Documents are not Required in IDS filed after October 21, 2004

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Translation ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
		JP 2000-150669		Not translated		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Translation ⁶
		Japanese Patent Office Notification of Reasons for Rejection and English translation thereof. (App'n. #2002-268970)	
		Ja-Hum Ku et al., "High Performance pMOSFETs with Ni(Si _{1-x} Ge _x)/Poly-Si _{0.8} Ge _{0.2} Gate," 2000 Symposium on VLSI Technology Digest of Technical Papers, 2000, pp. 114 to 115.	
		H. B. Zhao et al., "Interfacial reactions of Ni on Si _{1-x} Ge _x (x=0.2, 0.3) at low temperature by rapid thermal annealing," Journal of Applied Physics, July 1, 2002, Volume 92, Number 1, pp. 214-217.	

Examiner Signature	<i>S. Fle</i>	Date Considered	12/07/05
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